N-Channel Enhancement Mode Power MOSFET

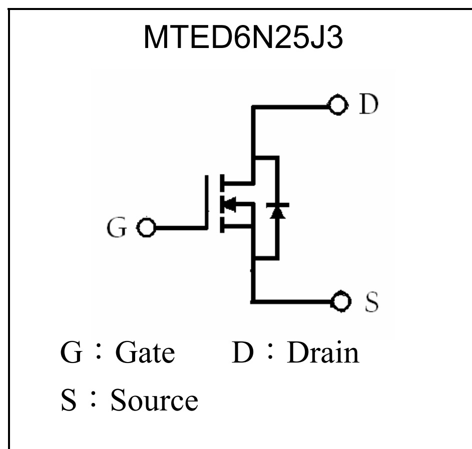
MTED6N25J3

BV_{DSS}		250V
I_D		8A
$R_{DSON(TYP)}$	V_{GS}=10V, I_D=5A	435mΩ
	V_{GS}=6V, I_D=3A	410mΩ

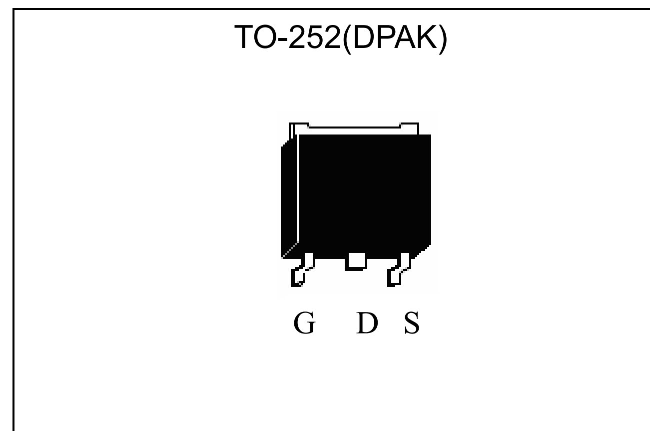
Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating and halogen-free package

Equivalent Circuit

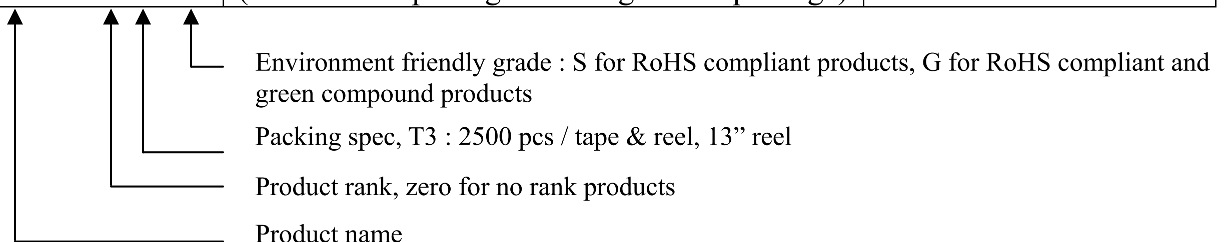


Outline



Ordering Information

Device	Package	Shipping
MTED6N25J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	250	V
Gate-Source Voltage	V_{GS}	±30	
Continuous Drain Current @ V_{GS}=10V, T_C=25°C (Note 1)	I_D	8	A
Continuous Drain Current @ V_{GS}=10V, T_C=100°C (Note 1)		5	
Continuous Drain Current @ V_{GS}=10V, T_A=25°C (Note 2)		1.5	
Continuous Drain Current @ V_{GS}=10V, T_A=70°C (Note 2)		1.2	
Pulsed Drain Current (Note 3)	I_{DM}	16	
Avalanche Current (Note 3)	I_{AS}	2	
Avalanche Energy @ L=50mH, I_D=2A, V_{DD}=50V (Note 2)	E_{AS}	100	mJ
Repetitive Avalanche Energy@ L=0.1mH (Note 3)	E_{AR}	2	
Total Power Dissipation @T_C=25℃ (Note 1)	P_D	78	W
Total Power Dissipation @T_C=100℃ (Note 1)		21	
Total Power Dissipation @T_A=25℃ (Note 2)	P_{DSM}	2.5	
Total Power Dissipation @T_A=70℃ (Note 2)		1.6	
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.6	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 2)	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 4)	$R_{\theta JA}$	110	°C/W

Note : 1.The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

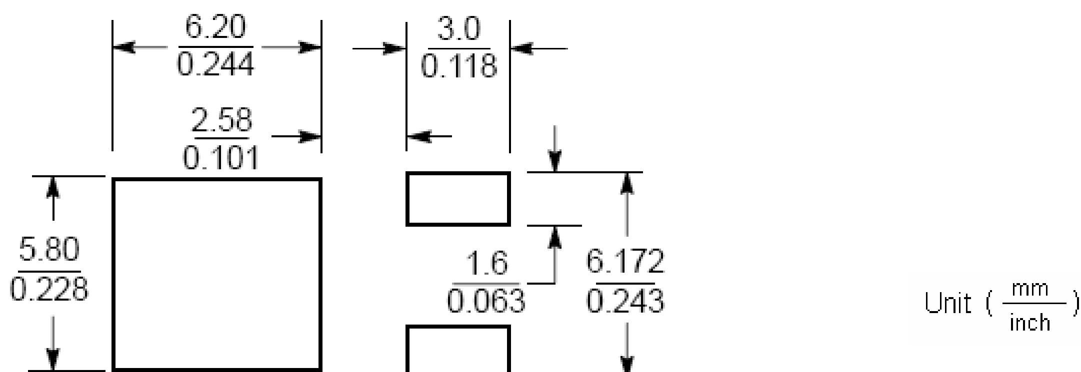
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.
4. When mounted on the minimum pad size recommended (PCB mount), t≤10s.

Characteristics (Tc=25°C, unless otherwise specified)

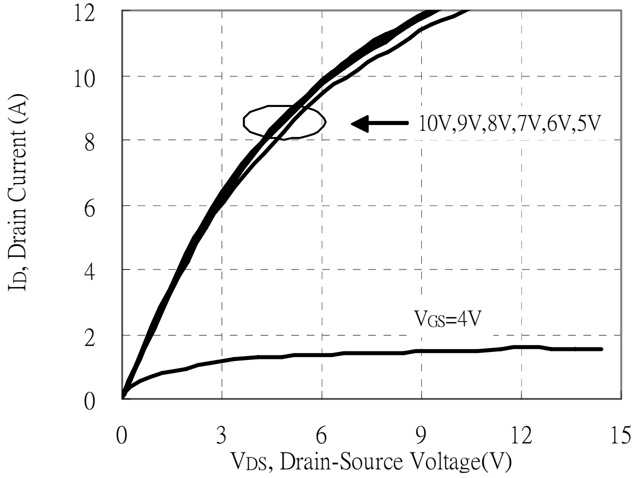
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	250	-	-	V	V_{GS}=0, I_D=250μA
$V_{GS(th)}$	2	3	4	V	V_{DS} =V_{GS}, I_D=250μA
I_{GSS}	-	-	±100	nA	V_{GS}=±30, V_{DS}=0
I_{DSS}	-	-	1	μA	V_{DS} =200V, V_{GS} =0
	-	-	25		V_{DS} =200V, V_{GS} =0, T_J=125°C
$R_{DS(ON)}$ *1	-	435	560	mΩ	V_{GS} =10V, I_D=5A
	-	410	530		V_{GS} =6V, I_D=3A
G_{FS} *1	-	2.5	-	S	V_{DS} =40V, I_D=1.5A
Dynamic					
Qg *1, 2	-	7.5	-	nC	V_{DS}=200V, I_D=1.5A, V_{GS}=10V
Qgs *1, 2	-	2.7	-		
Qgd *1, 2	-	2	-		
$t_{d(ON)}$ *1, 2	-	15	-	ns	V_{DS}=125V, I_D=1.5A, V_{GS}=10V, R_G=25Ω
tr *1, 2	-	12	-		
$t_{d(OFF)}$ *1, 2	-	42	-		
t_f *1, 2	-	20	-		
Ciss	-	579	-	pF	V_{GS}=0V, V_{DS}=25V, f=1MHz
Coss	-	44	-		
Crss	-	20	-		
Source-Drain Diode					
I_S *1	-	-	8	A	
I_{SM} *3	-	-	16		
V_{SD} *1	-	0.73	1	V	I_S=1A, V_{GS}=0V
trr	-	80	-	ns	I_F=1.5A, dI_F/dt=100A/μs
Qrr	-	290	-	nC	

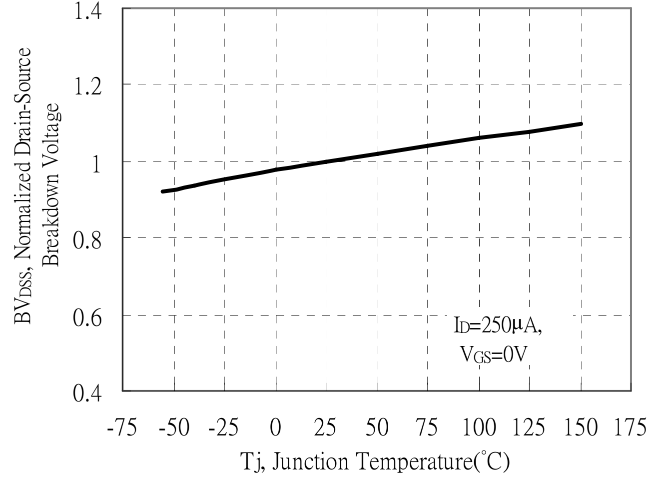
Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
*2.Independent of operating temperature
*3.Pulse width limited by maximum junction temperature.

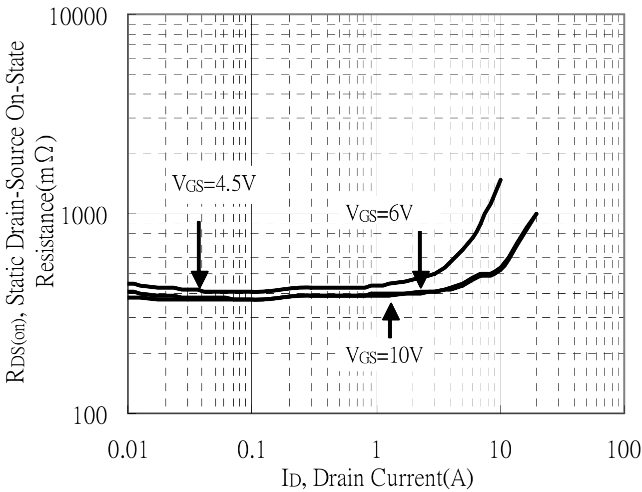
Recommended soldering footprint

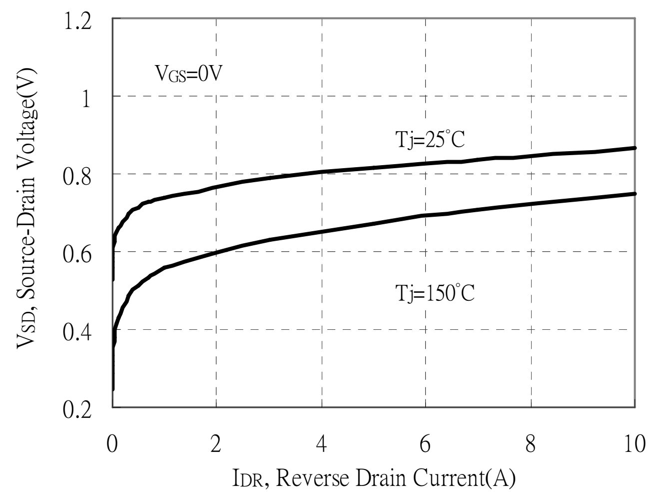


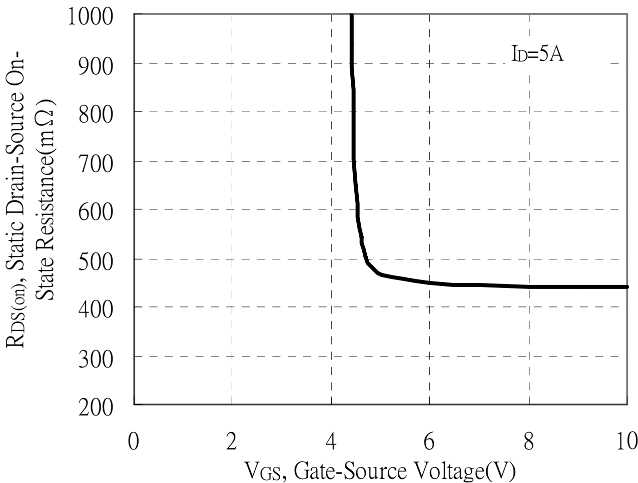
Typical Characteristics

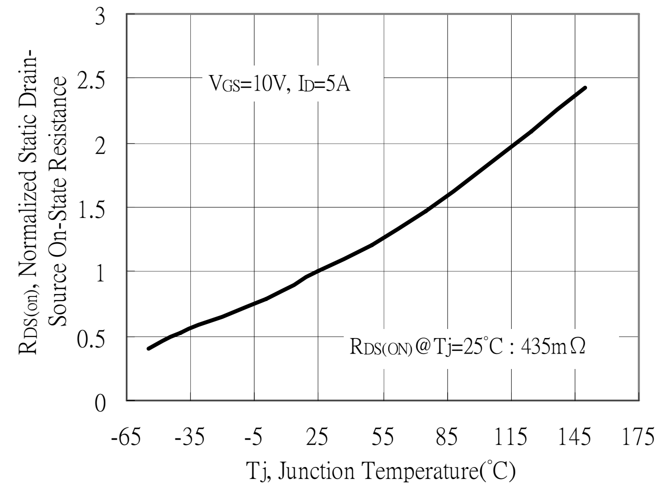












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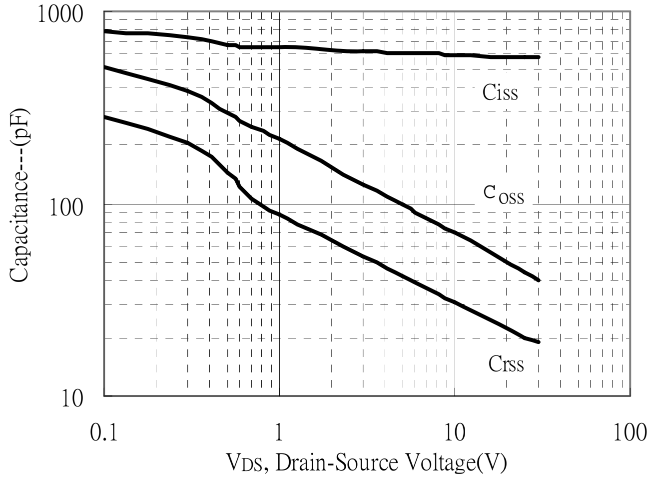

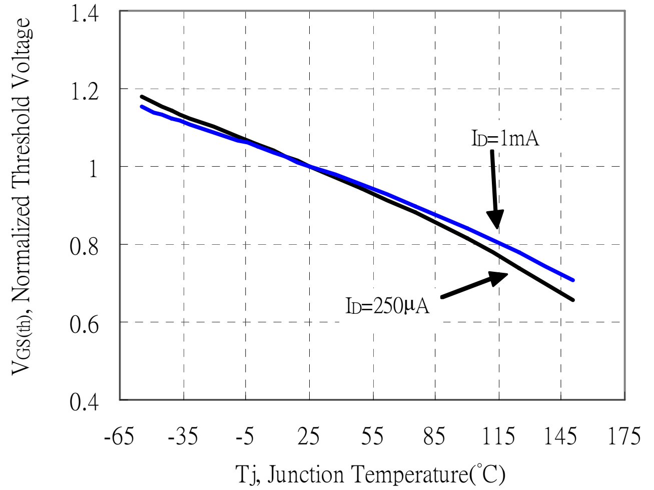

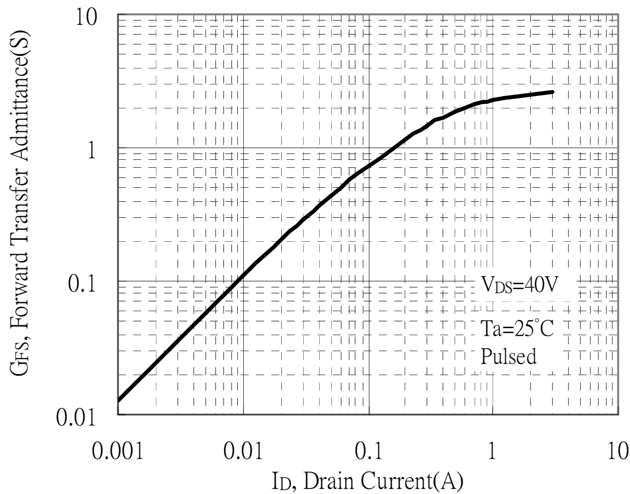

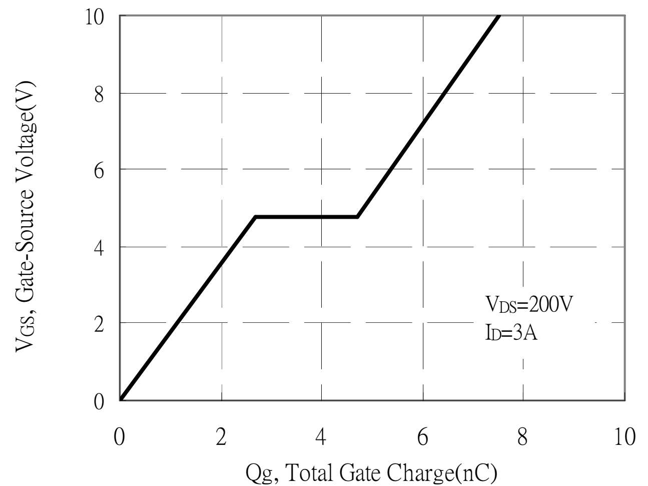

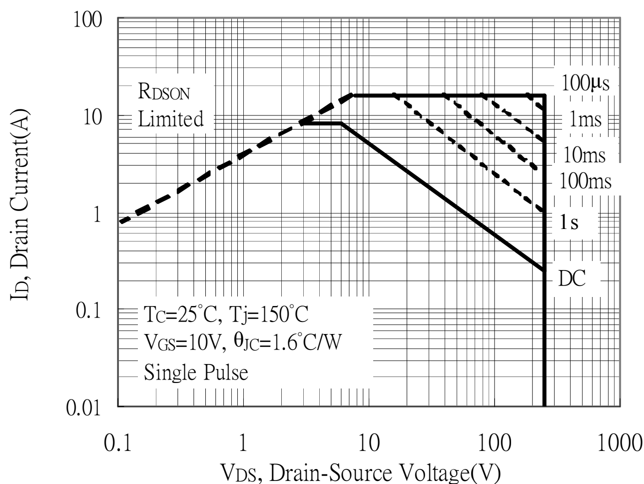

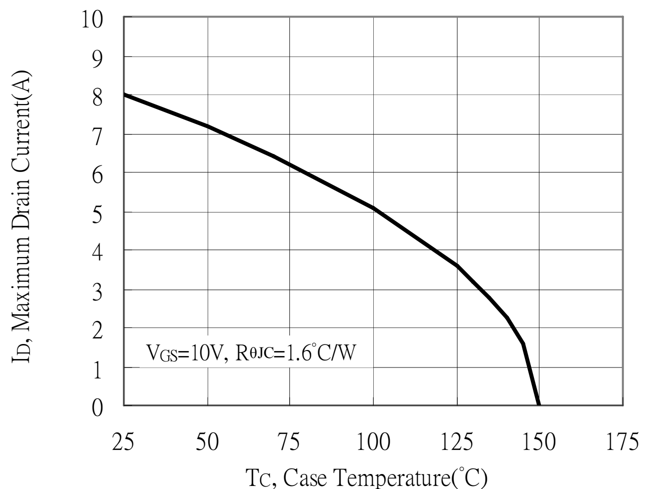

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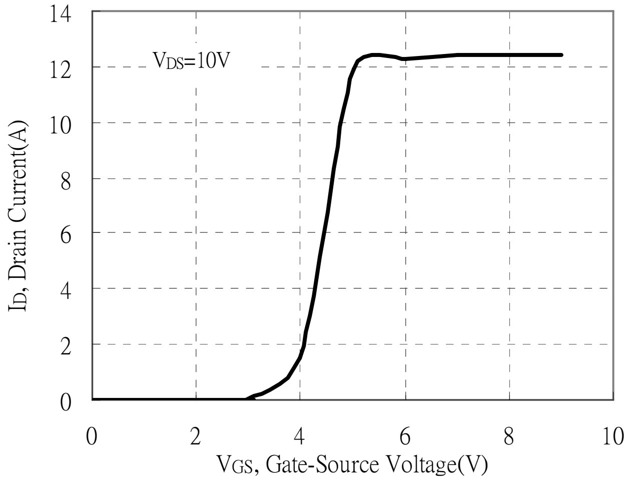
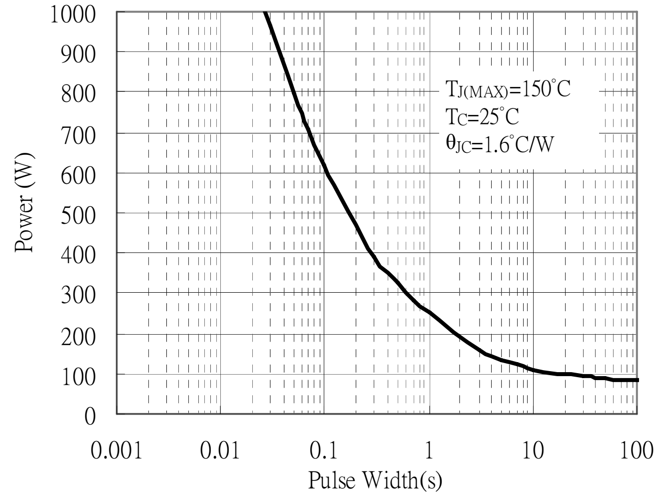
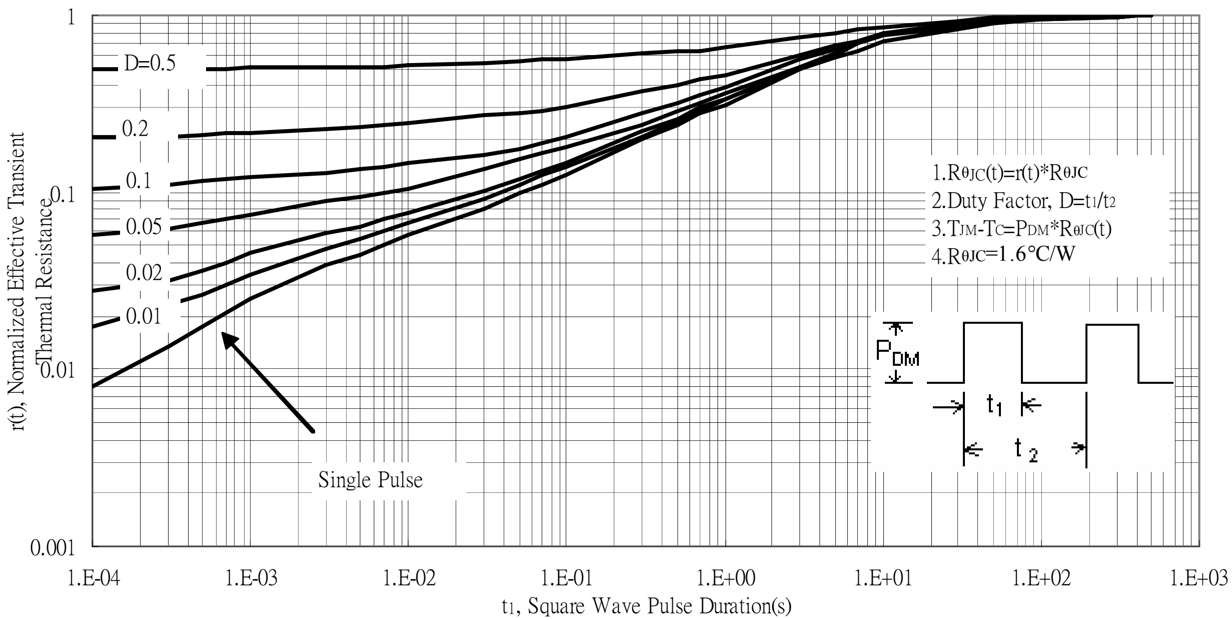
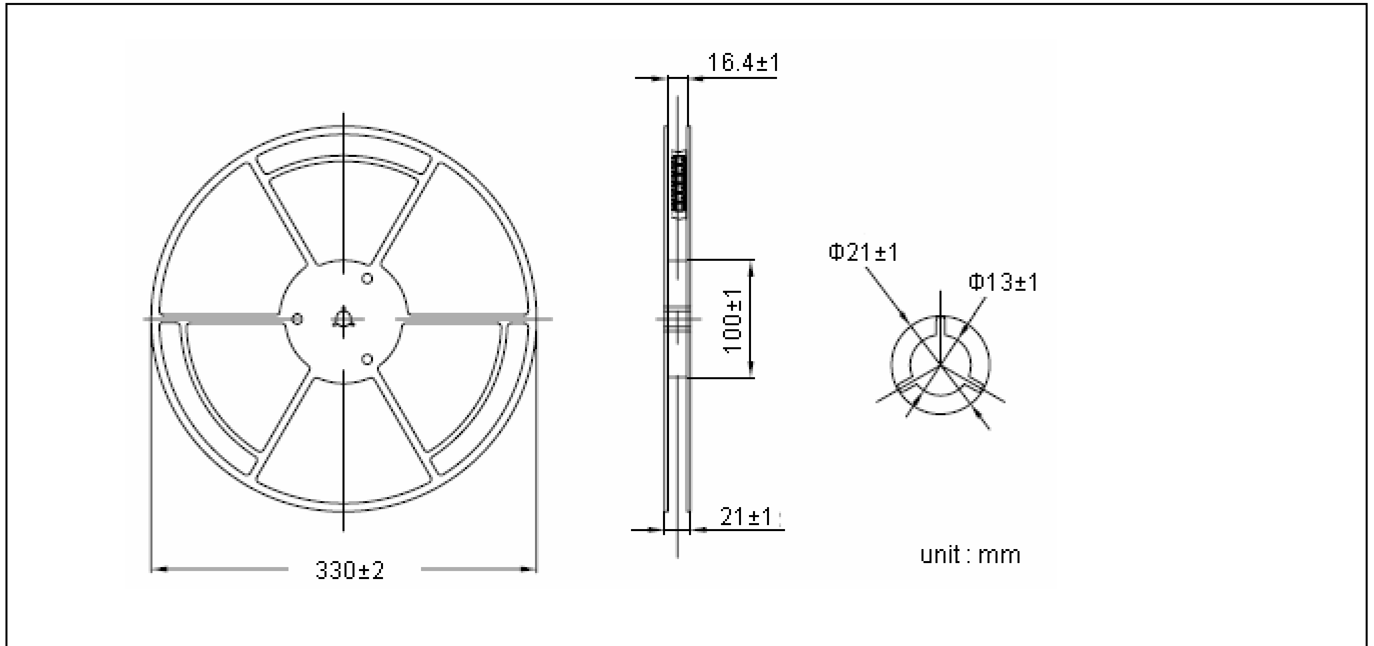


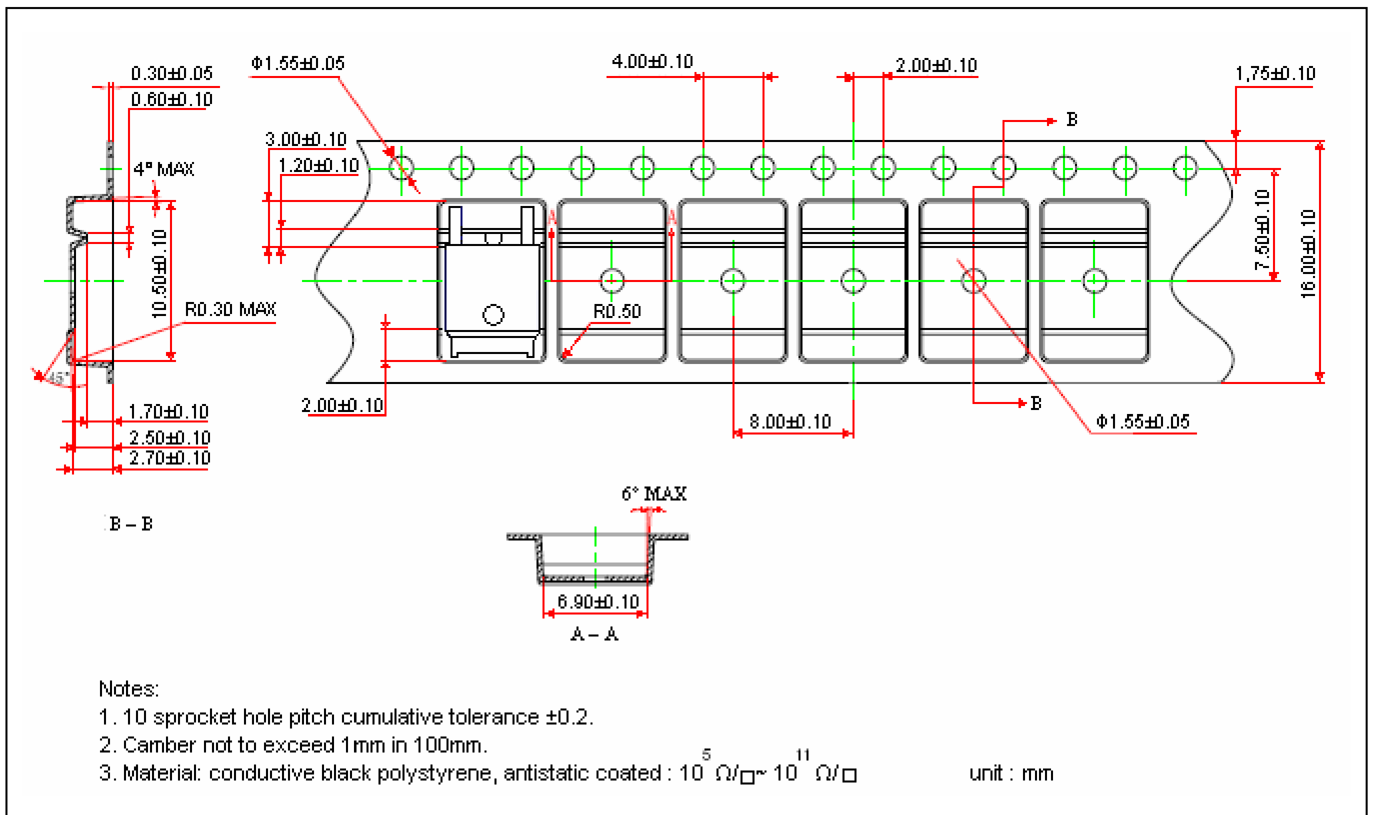




Reel Dimension



Carrier Tape Dimension



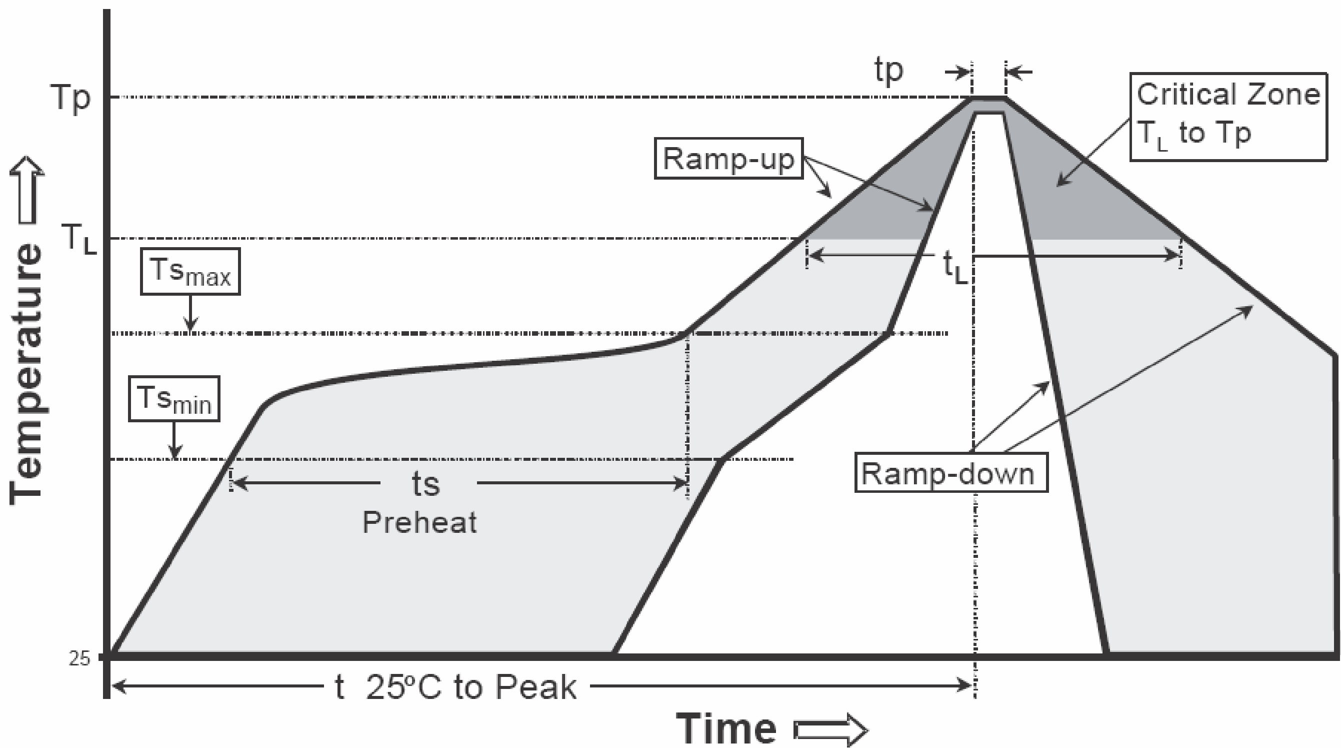
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene, antistatic coated : 10^5 Ω/□~ 10^{11} Ω/□

unit : mm

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

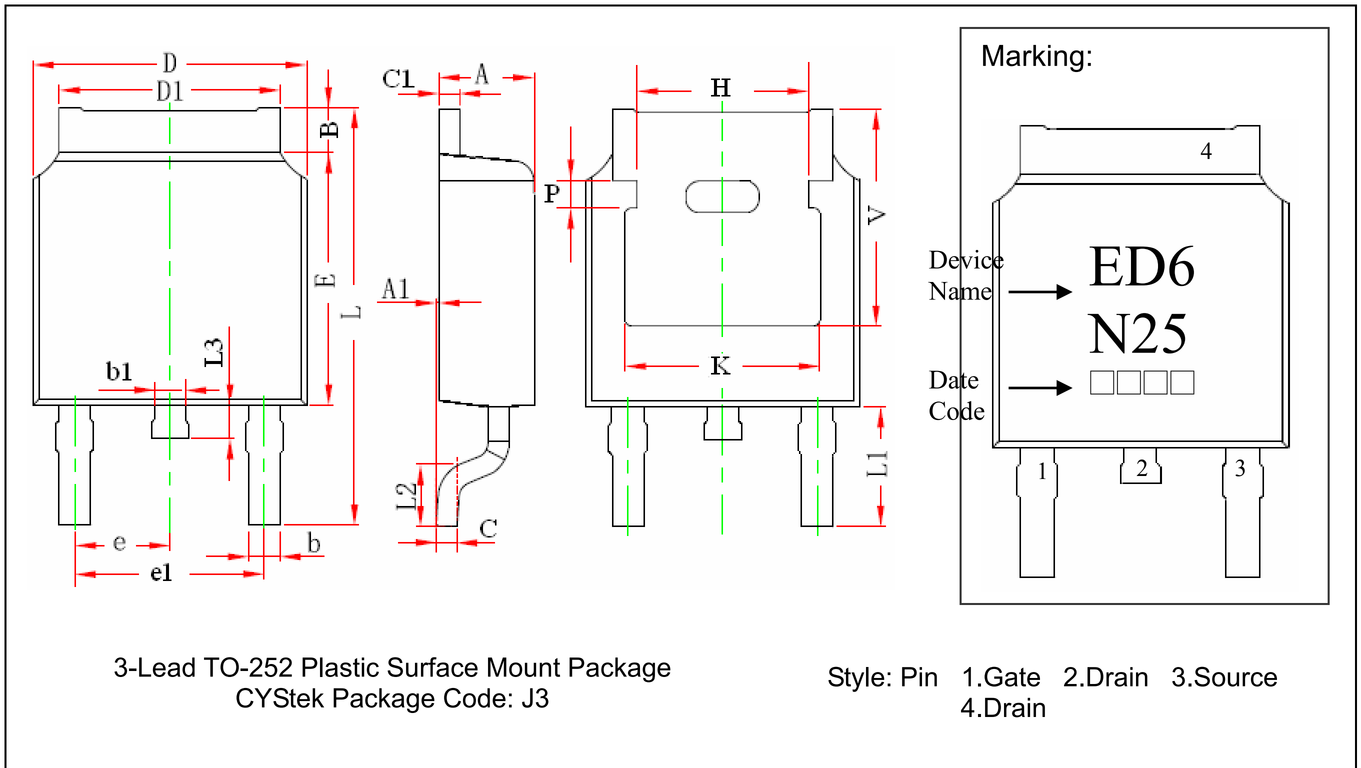
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package
CYStek Package Code: J3

Style: Pin 1.Gate 2.Drain 3.Source 4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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